

JUNCTION FIELD EFFECT TRANSISTOR 2SK1109

8.0

N-CHANNEL SILICON JUNCTION FIELD EFFECT TRANSISTOR FOR IMPEDANCE CONVERTER OF ECM

DESCRIPTION

The 2SK1109 is suitable for converter of ECM.

FEATURES

- · Compact package
- · High forward transfer admittance 1000 μ S TYP. (IDSS = 100 μ A) 1600 μ S TYP. (IDSS = 200 μ A)
- Includes diode and high resistance at G S

ORDERING INFORMATION

PART NUMBER	PACKAGE		
2SK1109	SC-59 (MM)		

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage Note	VDSX	20	V
Gate to Drain Voltage	Vgdo	-20	V
Drain Current	lσ	10	mΑ
Gate Current	lg	10	mΑ
Total Power Dissipation	PT	80	mW
Junction Temperature	T_j	125	°C
Storage Temperature	Tstg	-55 to +125	°C

PACKAGE DRAWING (Unit: mm)

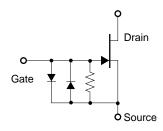
2.9 ± 0.2

1. Source

2. Drain

3. Gate

EQUIVALENT CIRCUIT



Note Vgs = -1.0 V

Remark Please take care of ESD (Electro Static Discharge) when you handle the device in this document.

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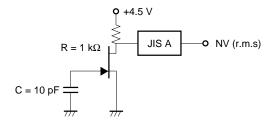
ELECTRICAL CHARACTERISTICS (TA = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS		TYP.	MAX.	UNIT
Zero Gate Voltage Drain Cut-off Current	IDSS	V _{DS} = 5.0 V, V _{GS} = 0 V	40		600	μΑ
Gate Cut-off Voltage	V _{GS(off)}	$V_{DS} = 5.0 \text{V}, I_{D} = 1.0 \mu\text{A}$	-0.1		-1.0	V
Forward Transfer Admittance	y fs1	$V_{DS} = 5.0 \text{ V}, \text{ ID} = 30 \ \mu\text{A}, \text{ f} = 1.0 \text{ kHz}$	350			μS
Forward Transfer Admittance	Yfs2	$V_{DS} = 5.0 V, V_{GS} = 0 V, f = 1.0 kHz$	350			μS
Input Capacitance	Ciss	V _{DS} = 5.0 V, V _{GS} = 0 V, f = 1.0 MHz		7.0	8.0	pF
Noise Voltage	NV	See Test Circuit		1.8	3.0	μV

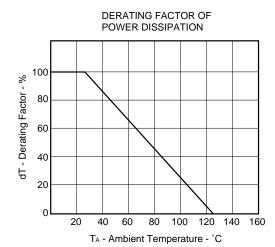
IDSS RANK

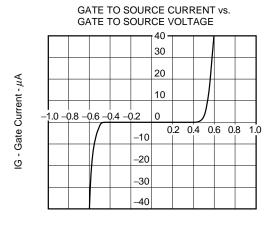
MARKING	J32	J33	J34	J35	J36	J37
Ioss (μA)	40 to 70	60 to 110	90 to 180	150 to 300	200 to 450	300 to 600

NOISE VOLTAGE TEST CIRCUIT

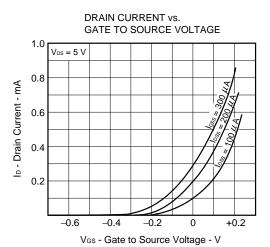


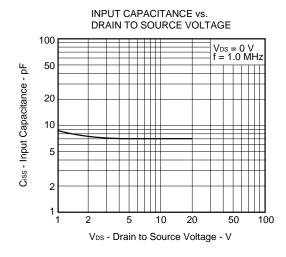
TYPICAL CHARACTERISTICS (TA = 25°C)



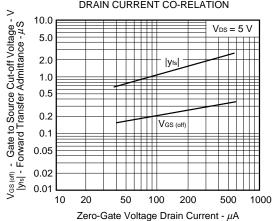


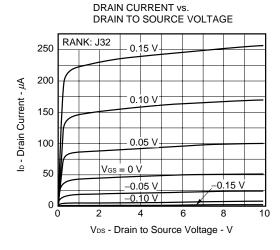
V_{GS} - Gate to Source Voltage - V

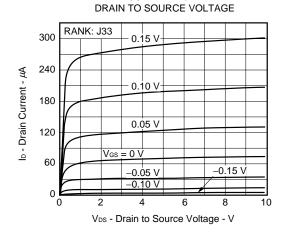




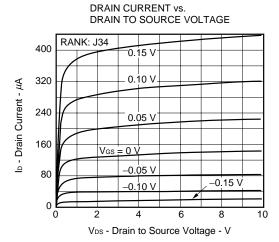
GATE TO SOURCE CUT-OFF VOLTAGE AND FORWARD TRANSFER ADMITTANCE vs. ZERO-GATE VOLTAGE DRAIN CURRENT CO-RELATION

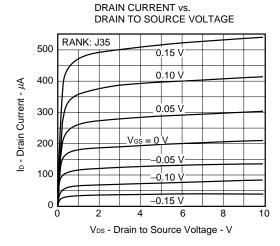


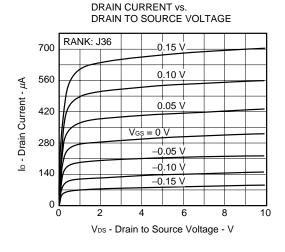


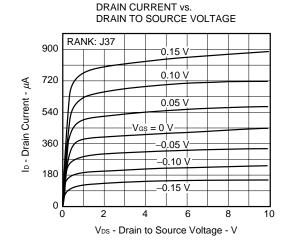


DRAIN CURRENT vs.









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